

AMENDMENTS TO THE CLAIMS

Please amend claims 1 and 13 as follows:

1. (currently amended) A semiconductor device, comprising:
a semiconductor substrate;
at least one of a protruding electrode and wiring formed on one surface of the semiconductor substrate; and
a first resin film formed on the one surface of the semiconductor substrate,
wherein the first resin film has elasticity lower than 5 GPa so as to limit stress induced by a difference in thermal expansion coefficient between the semiconductor substrate and the first resin film.

Claim 2 (canceled)

3. (previously presented) A semiconductor device, comprising:
a semiconductor substrate;
at least one of a protruding electrode and wiring formed on one surface of the semiconductor substrate; and
a first resin film formed on the one surface of the semiconductor substrate,
wherein the first resin film has elasticity low enough to reduce stress induced by a difference in thermal expansion coefficient between the semiconductor substrate and the first resin film, and

wherein a second resin film having one of higher elasticity and higher strength than the first resin film is formed on the other surface of the semiconductor substrate.

4. (original) The semiconductor device according to claim 3, wherein an elastic modulus of the second resin film is 15 GPa or higher.

5. (original) The semiconductor device according to claim 1, wherein the semiconductor substrate has a thickness of 550 μm or less.

6. (original) The semiconductor device according to claim 3, wherein the semiconductor substrate has a thickness of 200 μm or less and is placed at a center of the semiconductor device in a thickness direction of a cross section thereof.

Claim 7 (canceled)

8. (previously presented) A semiconductor device, comprising:
a semiconductor chip; an electrode pad formed on the semiconductor chip;
a resin film formed to cover a surface of the semiconductor chip;
a post bonded to the electrode pad and provided to penetrate through the resin film, a portion of which in close proximity to a junction portion with the electrode pad is made of gold; and

a passivation layer on the surface of the semiconductor chip, between the semiconductor chip and the resin film and covered by the resin film so as to have a passivation film/resin film interface therewith, the gold portion of the post including a portion facing the passivation film/resin film interface.

9. (original) The semiconductor device according to claim 8, wherein the post includes a portion made of a metal material other than gold.

10. (original) The semiconductor device according to claim 8, wherein the post includes a junction portion provided on a side of the electrode pad and made of gold, a tip end portion provided on a side of a tip end and made of gold, and an intermediate portion provided between the junction portion and the tip end portion and made of a metal material other than gold.

11. (previously presented) The semiconductor device according to claim 8, wherein the passivation layer has a thickness greater than a thickness of the electrode pad and the gold portion of the post projects below a surface of passivation layer at the passivation film/resin film interface into direct contact with the electrode pad.

12. (previously presented) The semiconductor device according to claim 8, wherein the passivation layer has a thickness greater than a thickness of the electrode pad and the

gold portion of the post projects below a surface of passivation layer at the passivation film/resin film interface into confrontation with the electrode pad.

13. (currently amended) A semiconductor device according to claim [[1]] &, wherein the resin film is a first resin film, further comprising a second resin film having one of higher elasticity and higher strength than the first resin film [[is]] formed on the other surface of the semiconductor substrate.